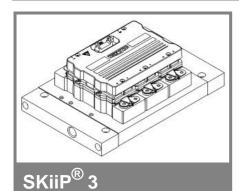
SKiiP 1803GB172-3DW V3



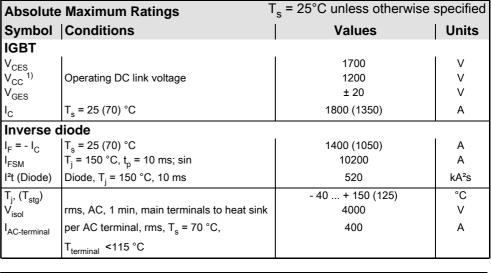
2-pack-integrated intelligent Power System

Power section SKiiP 1803GB172-3DW V3

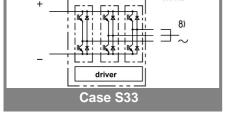
Preliminary Data

Power section features

- SKiiP technology inside
- Trench IGBTs
- CAL diode technology
- · Integrated current sensor
- · Integrated teperature sensor
- Integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiiP[®] 3 System)
- IEC 60068-1 (climate) 40/125/56
- UL recognized file no. E63532
- with assembly of suitable MKP capacitor per terminal
- 8) AC connection busbars must be connected by the user; copper busbars available on request



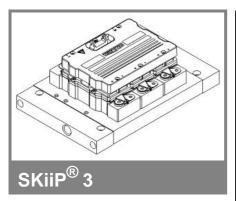
Characteristics				$T_s = 25$ °C unless otherwise specified				
Symbol	Conditions			min.	typ.	max.	Units	
IGBT								
V _{CEsat}	I _C = 900 A, T _j = 25 (125) °C; measured at terminal					1,9 (2,2)	2,4	V
V_{CEO}	T _i = 25 (125) °C; at terminal					1 (0,9)	1,2 (1,1)	V
r_{CE}		25) °C; at t				1 (1,4)	1,3 (1,7)	mΩ
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES} , T _i = 25 (125) °C					3,6 (216)		mA
E _{on} + E _{off}	I _C = 900 A, V _{CC} = 900 V					mJ		
	T _j = 125 °C, V _{CC} = 1200 V					mJ		
R _{CC+EE}	terminal chip, T _i = 25 °C					0,17		mΩ
L _{CE}	top, bottor	m				4		nH
C _{CHC}	per phase, AC-side					3		nF
Inverse diode								
$V_F = V_{EC}$	I _F = 900 A measured at	, T _j = 25 (1 terminal	25) °C			2 (1,8)	2,15	V
V_{TO}	T _i = 25 (12	T _i = 25 (125) °C				1,1 (0,8)	1,2 (0,9)	V
r _T	T _i = 25 (125) °C					1 (1,1)	1,1 (1,2)	mΩ
E _{rr}	I _C = 900 A, V _{CC} = 900 V					108		mJ
	T _j = 125 °C, V _{CC} = 1200 V					128		mJ
Mechani	cal data							
M_{dc}	DC terminals, SI Units				6		8	Nm
M _{ac}	AC terminals, SI Units				13		15	Nm
W	SKiiP® 3 System w/o heat sink					2,4		kg
W	heat sink					5,2		kg
Thermal characteristics (NWK 40; 8l/min; 50%glyc); "s" reference to heat sink; "r" reference to built-in temperature sensor (acc.IEC 60747-15)								
	•	e to bui	ıτ-ın tem	perature	e sensor	(acc.IEC		
R _{th(j-s)I}	per IGBT						0,017	K/W
R _{th(j-s)D}	per diode	. / 1	\				0,033	K/W
Z_{th}	R _i (mK/W) (max. values) 1 2 3 4				4	tau 2	•	,
7	1,4	∠ 6,8	3 7,8	4 0	1 69	2 0,35	3 0,02	4 1
$Z_{\text{th(j-r)l}}$ $Z_{\text{th(j-r)D}}$	2,6	4	7,8 17,7	17,7	50	0,33 5	0,02	0.04
	4.6	4,7	1,1	0.6	48	15	2,8	0,4
$Z_{th(r-a)}$	٦,0	4,1	1,1	0,0	40	13	۷,0	0,4



^{*} The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

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SKiiP 1803GB172-3DW V3



2-pack-integrated intelligent Power System

2-pack integrated gate driver SKiiP 1803GB172-3DW V3

Preliminary Data

Gate driver features

- CMOS compatible inputs
- Wide range power supply
- Integrated circuitry to sense phase current, heat sink temperature and

DC-bus voltage (option)

- Short circuit protection
- · Over current protection
- Over voltage protection (option)
- Power supply protected against under voltage
- Interlock of top/bottom switch
- · Isolation by transformers
- Fibre optic interface (option for GB-types only)
- IEC 60068-1 (climate) 40/85/56

Absolute	Maximum Ratings	_a = 25°C unless otherwise specified		
Symbol	Conditions	Values	Units	
V_{S2}	unstabilized 24 V power supply	30	V	
V_{i}	input signal voltage (high)	15 + 0,3	V	
dv/dt	secondary to primary side	75	kV/μs	
V_{isollO}	input / output (AC, rms, 2s)	4000	V	
V _{isoIPD}	partial discharge extinction voltage, rms, Q _{PD} ≤10 pC;	1500	V	
V _{isol12}	output 1 / output 2 (AC, rms, 2s)	1500	V	
f _{sw}	switching frequency	9	kHz	
f _{out}	output frequency for I _{peak(1)} =I _C	9	kHz	
$T_{op} (T_{stg})$	operating / storage temperature	- 40 + 85	°C	

Characte	eristics	(T _a = 25°			
Symbol	Conditions	min.	typ.	max.	Units
V_{S2}	supply voltage non stabilized	13	24	30	V
I _{S2}	V _{S2} = 13V - 30V	258+46*f/kHz+0,000145*(I _{AC} /A) ²			mA
V _{iT+}	input threshold voltage (High)			12,3	V
V_{iT-}	input threshold voltage (Low)	4,6			V
R _{IN}	input resistance		10		kΩ
C_{IN}	input capacitance		1		nF
t _{d(on)IO}	input-output turn-on propagation time		1,5		μs
$t_{d(off)IO}$	input-output turn-off propagation time		1,5		μs
t _{pERRRESET}	error memory reset time		12,2		μs
t_{TD}	top / bottom switch interlock time		3,3		μs
I _{analogOUT}	max. 5mA; 8 V corresponds to 15 V supply		1500		Α
	voltage for external components				
I _{s1out}	max. load current			50	mA
I _{TRIPSC}	over current trip level				
	$(I_{analog} OUT = 10 V)$		1875		Α
T_tp	over temperature protection	110		120	°C
U _{DCTRIP}	U_{DC} -protection ($U_{analog OUT} = 9 V$);		not implemented	i	V
	(option for GB types)				

For electrical and thermal design support please use SEMISEL. Access to SEMISEL is via SEMIKRON website http://www.semikron.com.

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